

UHF power transistor

BLW81

Description:

N-P-N silicon planar epitaxial transistor intended for transmitting applications in class-A, B or C in the UHF and VHF range for nominal supply voltages up to 13.5 V. The resistance stabilization of the transistor provides protection against device damage at severe load mismatch conditions.

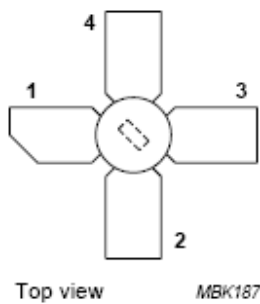
Features:

The transistor is housed in a 1/4" capstan envelope with a ceramic cap.

Data:

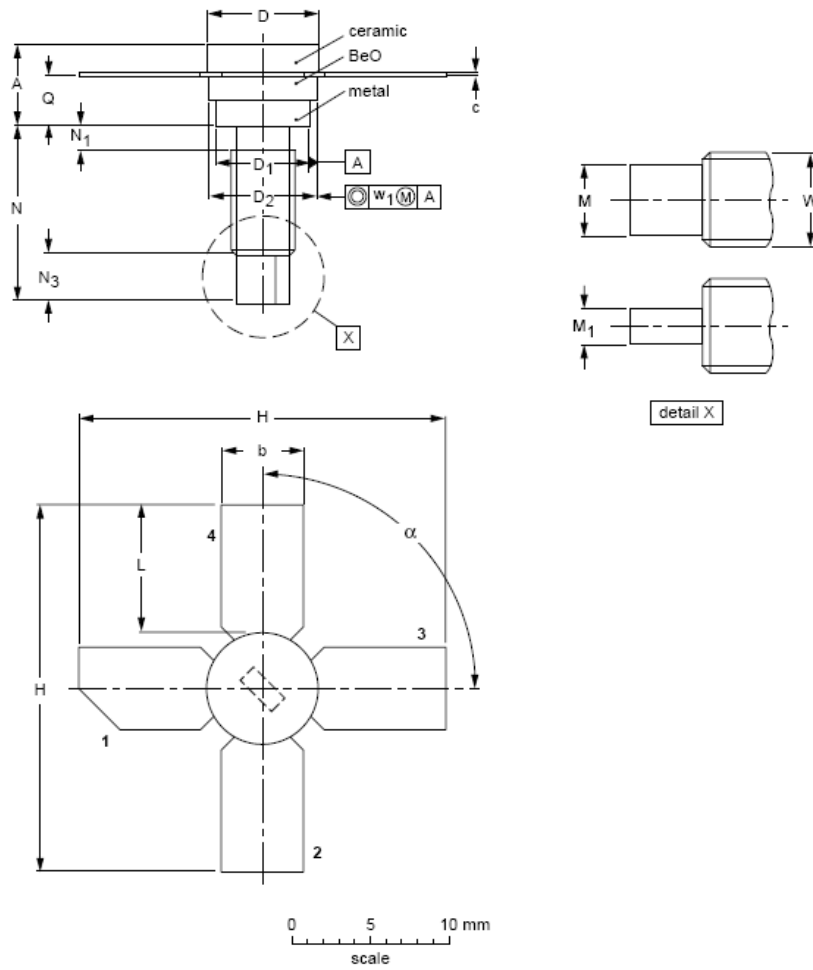
MODE OF OPERATION	V _{CE} V	f MHz	P _L W	G _p dB	η %	\bar{z}_i Ω	\bar{Y}_L mS
c.w.	12,5	470	10	> 6,0	> 60	1,3 + j2,5	150 – j66
c.w.	12,5	175	10	typ. 13,5	typ. 60	1,2 – j0,6	140 – j80

Drawings:



PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

Fig.1 Simplified outline. SOT122A.



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	D ₂	H	L	M ₁	M	N	N ₁ max.	N ₃	Q	W	w ₁	α
mm	5.97 4.74	5.85 5.58	0.18 0.14	7.50 7.23	6.48 6.22	7.24 6.93	27.56 25.78	9.91 9.14	3.18 2.66	1.66 1.39	11.82 11.04	1.02	3.86 2.92	3.38 2.74	8-32 UNC	0.381	90°